

# U232

## N-Channel Dual Silicon Junction Field-Effect Transistor

- **Differential Amplifier**
- **Low & Maximum Frequency Amplifier**

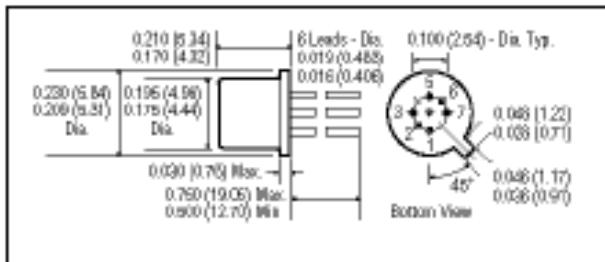
**Absolute maximum ratings at T<sub>A</sub> = 25°C**  
 Reverse Gate Source & Gate Drain Voltage -50V  
 Continuous Forward Gate Current 50 mA  
 Continuous Device Power Dissipation 300 mW  
 Power Derating 1.7 mW/°C  
 Storage Temperature Range -65°C to +150°C

| At 25°C free air temperature      |                      | U232 |     |      | Process NJ16 |  |
|-----------------------------------|----------------------|------|-----|------|--------------|--|
|                                   |                      | Min  | Typ | Max  | Unit         | Test Conditions                                |
| Gate Source Breakdown Voltage     | V <sub>(BR)GSS</sub> | -50  |     |      | V            | I <sub>G</sub> = -1 uA, V <sub>DS</sub> = 0 V  |
| Gate Reverse Current              | I <sub>GSS</sub>     |      |     | -0.1 | nA           | V <sub>GS</sub> = -10 V, V <sub>DS</sub> = 0 V |
| Gate Source Cutoff Voltage        | V <sub>GS(OFF)</sub> | -0.5 |     | -4.5 | V            | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V  |
| Drain Saturation Current (pulsed) | I <sub>DSS</sub>     | 0.5  |     | 5    | mA           | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V  |

### Dynamic Electrical Characteristics

|  |                  |   |  |    |        |   |            |
|--|------------------|---|--|----|--------|---|------------|
| Common-Source Forward Transconductance       | g <sub>fs</sub>  | 1 |  | 3  | mS     | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V | f = 1 kHz  |
| Common-Source Input Capacitance              | C <sub>iss</sub> |   |  | 6  | pF     | V <sub>DS</sub> = 10V, I <sub>D</sub> = 5 mA  | f = 1 MHz  |
| Common-Source Reverse Transfer Capacitance   | C <sub>rss</sub> |   |  | 2  | pF     | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 5 mA | f = 1 MHz  |
| Equivalent Short Circuit Input Noise Voltage | ~e <sub>N</sub>  |   |  | 80 | nV/√Hz | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 5 mA | f = 100 Hz |

| Matching Characteristics                          |   | Min | Max | Units | Test Conditions                                 |
|---|---|-----|-----|-------|---|
| Differential Gate-Source Voltage                  | (VGS1-VGS2)                             |     | 10  | mV    | V <sub>DS</sub> = 10 V, I <sub>D</sub> = -10 mA |
| Differential Gate Source Voltage with Temperature | $\frac{\Delta  VGS1 - VGS2 }{\Delta T}$ |     | 25  | μV/°C | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 30 μA  |



**TO-71 Package**  
 Dimensions in inches (mm)  
**Pin Configuration**  
 1 Source, 2 Drain, 3 Gate,  
 5 & 6 Drain, 6 Drain, 7 Gate

**Surface Mount Version:**  
 SMPU232



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